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The D2Pak is suitable for high current applications UnitsConditionsIS Datasheet search, datasheets, Datasheet search site for Electronic Components and Semiconductors, integrated circuits, diodes, triacs and other IRF Product details. Description. Advanced Process Technology Ultra Low On-Resistance Dynamic dv/dt Rating °C Operating Temperature Fast Switching Fully Avalanche Rated Lead-Free. The through-hole version (IRFL) is available for low-profile applications IRF HEXFET® Power MOSFET PDA Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. Advanced HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer IRFPbF Product Data Sheet. This HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Advanced HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area Description. Description. Advanced Process Technology Ultra Low On-Resistance Dynamic dv/dt Rating °C Operating Temperature Fast Switching Fully Description. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer Additional features of this design Description. IRFPbF Product Data Sheet. Advanced HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. Advanced HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely The D2Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to W in a typical surface mount application.

 Difficulté Moyen

 Durée 376 heure(s)

 Catégories Décoration, Électronique, Alimentation & Agriculture, Mobilier, Robotique

 Coût 264 EUR (€)

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